

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 11-031691

(43)Date of publication of application : 02.02.1999

(51)Int.Cl.

H01L 21/316

H01L 29/78

(21)Application number : 09-189954

(71)Applicant : FUJI ELECTRIC CO LTD

(22)Date of filing : 15.07.1997

(72)Inventor : UENO KATSUNORI

(30)Priority

Priority number : 09123619

Priority date : 14.05.1997

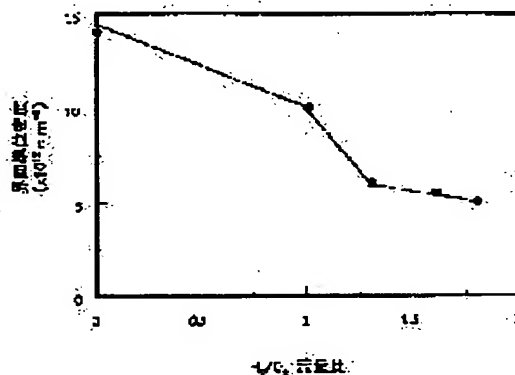
Priority country : JP

(54) METHOD FOR FORMING THERMAL OXIDIZED FILM FOR SILICON CARBIDE SEMICONDUCTOR DEVICE

(57)Abstract:

PROBLEM TO BE SOLVED: To reduce surface level density after the formation of a thermal, oxidized film for a silicon carbide semiconductor device.

SOLUTION: A thermal oxidized film forming method consists of growing a silicon oxide film by pyrogenic oxidation which causes thermal oxidation by introducing hydrogen oxygen. The flow ratio of hydrogen and oxygen is set 1:1, the flow of hydrogen is made larger than that of oxygen. After oxidation, the film is cooled in an atmosphere containing hydrogen at a rate in the range of 0.3-3°C/min. The temperature for taking the film out after cooling is set to 900°C or less.



LEGAL STATUS

[Date of request for examination]

08.08.2002

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

3491050

[Date of registration]

14.11.2003

[Number of appeal against examiner's decision]

of rejection]

[Date of requesting appeal against examiner's
decision of rejection]

[Date of extinction of right]

Copyright (C); 1998,2003 Japan Patent Office